

Supporting Information

Figure S1. Representative scanning electron microscope (SEM) image of products grown from an InP source at 540 °C on glass substrate (scale bar = 2 μ m).

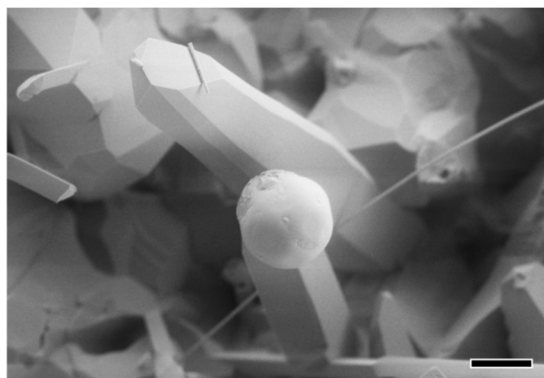


Figure S2. High-angle annular dark field scanning transmission electron microscopy (HAAD-STEM) image and energy dispersive X-ray (EDX) analyses of InP wires grown on Si substrate at 440°C (C and Cu signals arise from the Transmission electron microscopy (TEM) grid and partial surface contamination due to air exposure).

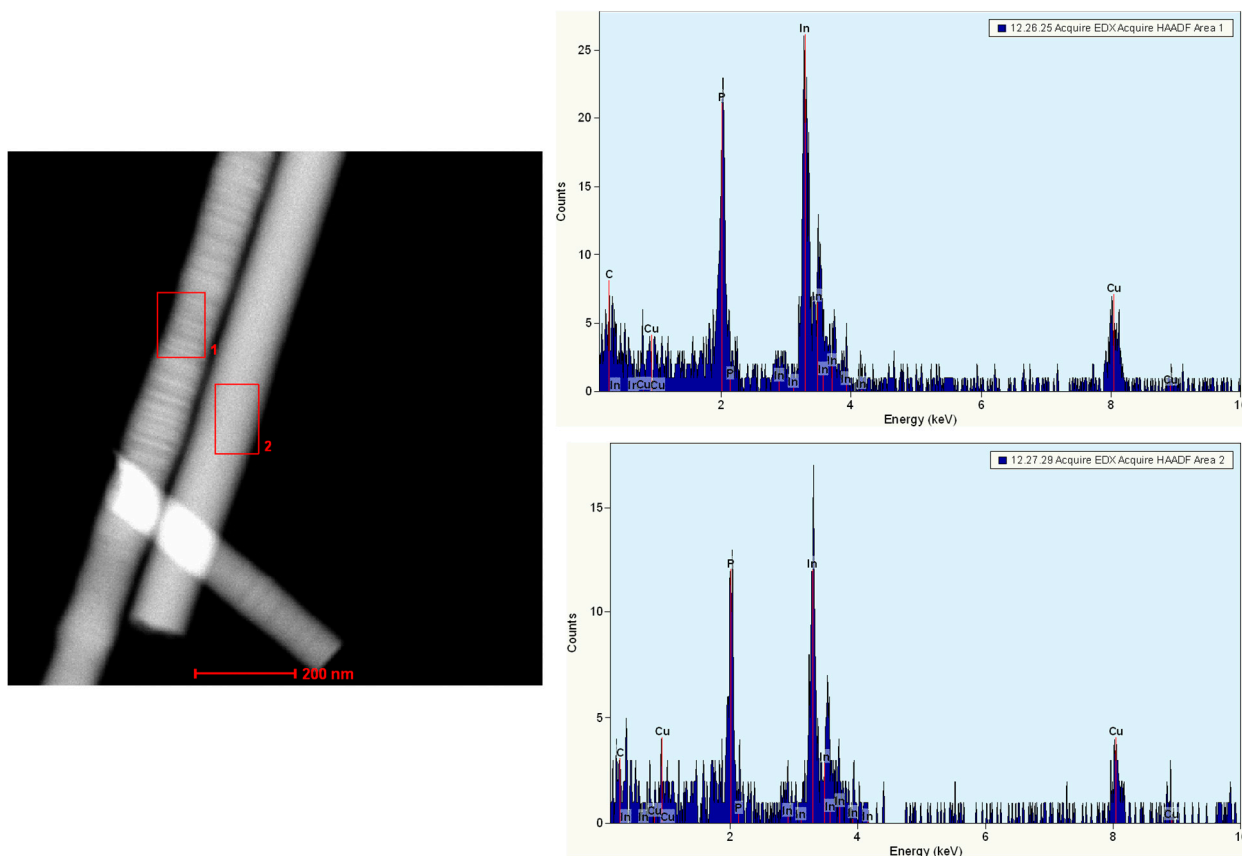


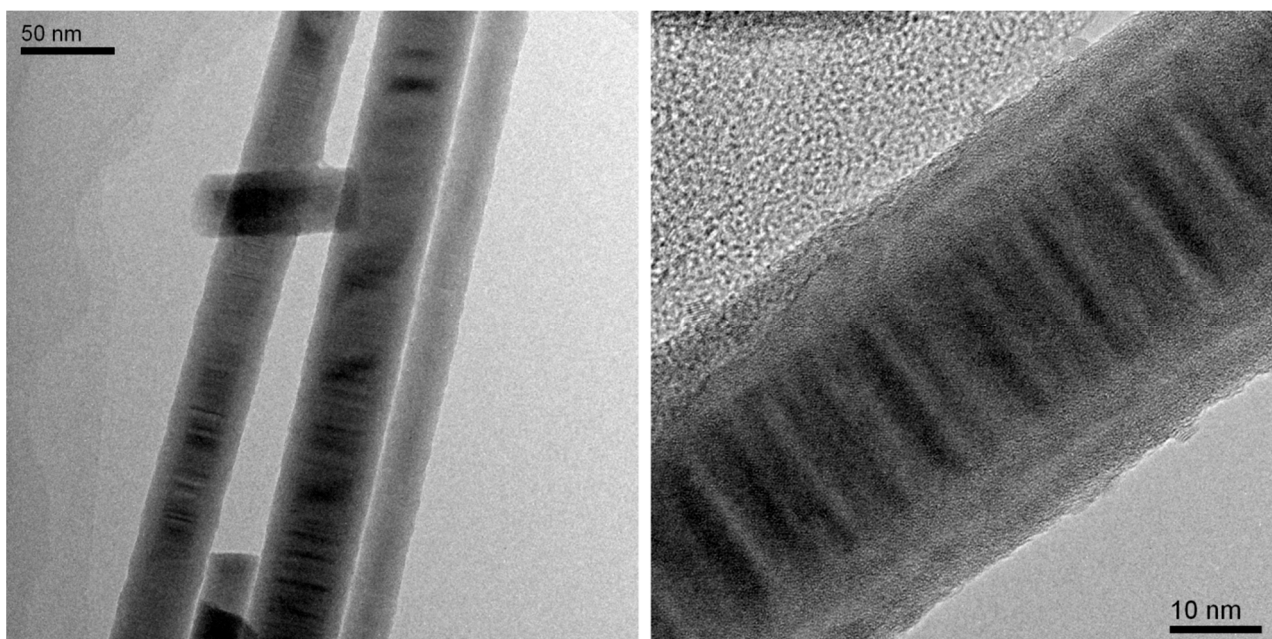
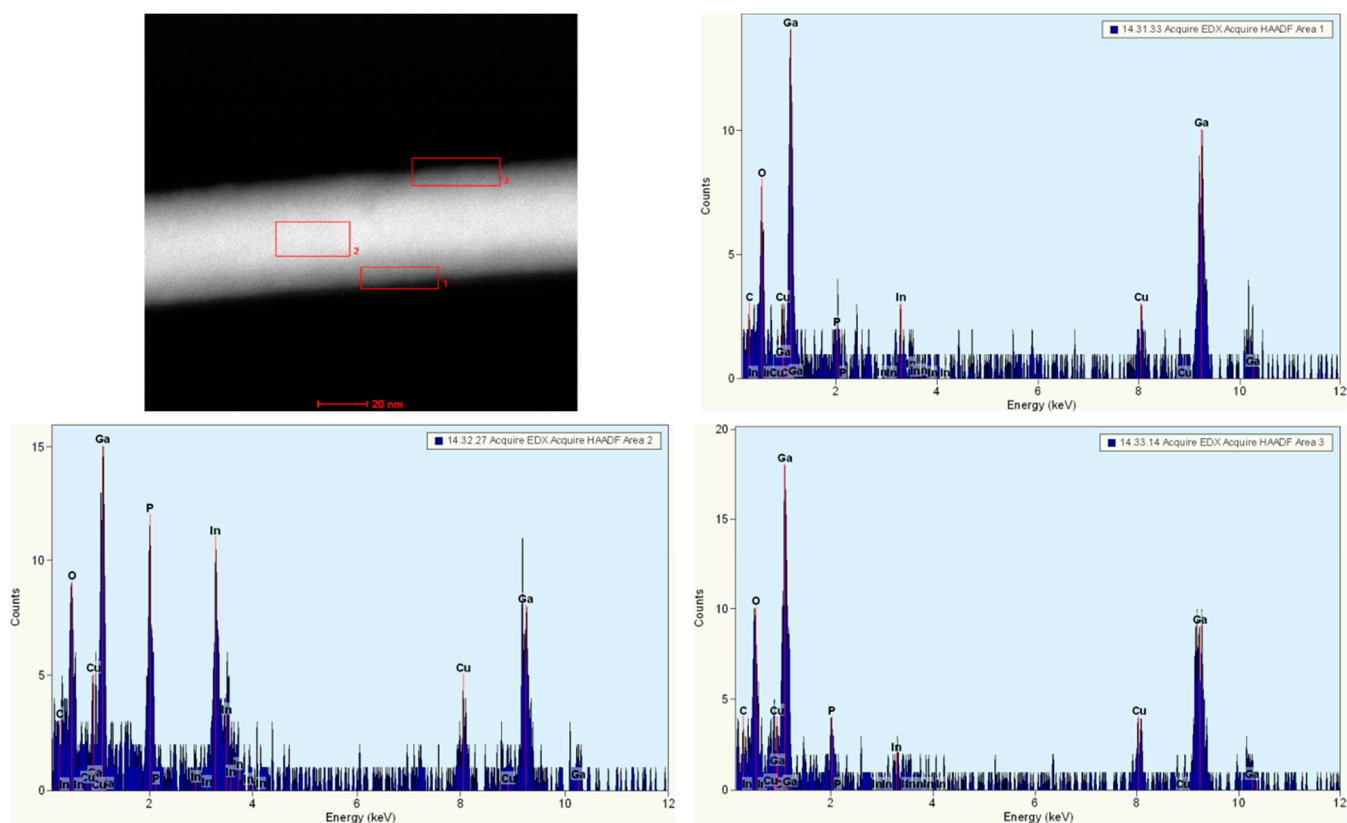
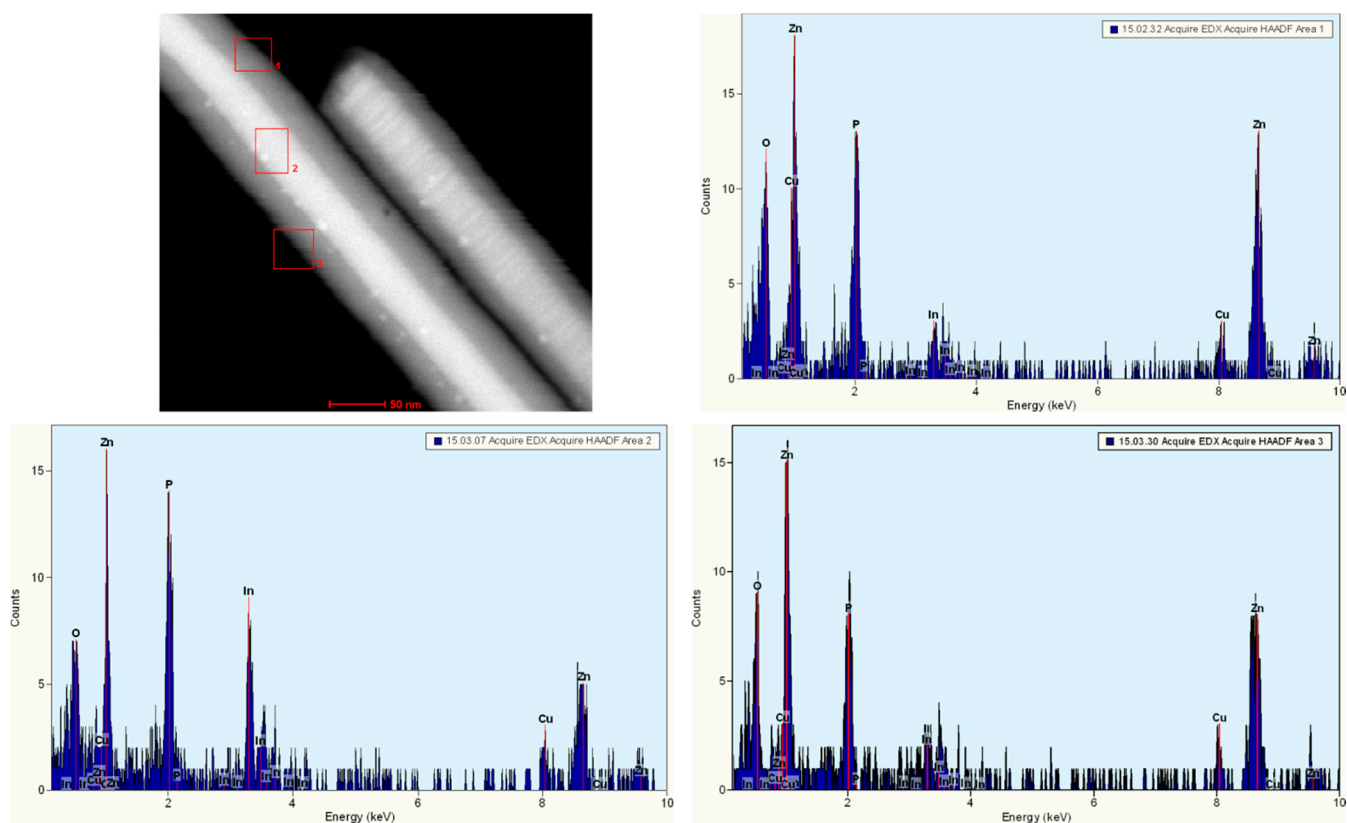
Figure S3. Representative TEM images of InP–Ga nanowires.**Figure S4.** Scanning transmission electron microscopy energy dispersive X-ray (STEM-EDX) analyses of InP–Ga nanowires (grown on Si substrate at 350 °C).

Figure S5. STEM-EDX analyses of InP-Zn wires (grown on Si substrate at 400° C).

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